

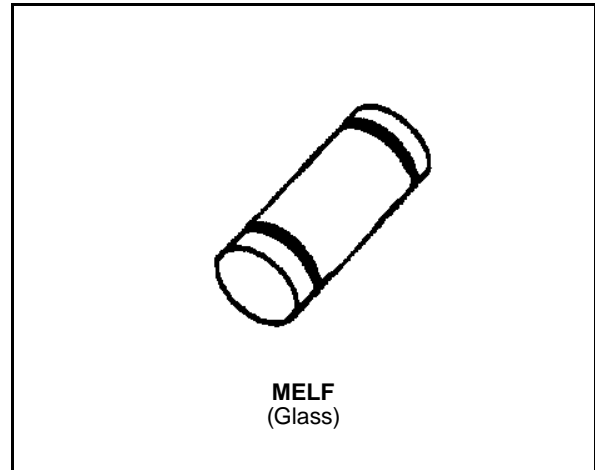


## TMBYV 10-60

### SMALL SIGNAL SCHOTTKY DIODE

#### DESCRIPTION

Metal to silicon rectifier diode in glass case featuring very low forward voltage drop and fast recovery time, intended for low voltage switching mode power supply, polarity protection and high frequency circuits.



#### ABSOLUTE MAXIMUM RATINGS (limiting values)

Symbol	Parameter	Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage	60	V
$I_{F(AV)}$	Average Forward Current	$T_i = 25\text{ }^\circ\text{C}$ 1	A
$I_{FSM}$	Surge non Repetitive Forward Current	$T_i = 25\text{ }^\circ\text{C}$ $t_p = 10\text{ms}$ 20 Sinusoidal Pulse	A
		$T_i = 25\text{ }^\circ\text{C}$ $t_p = 300\mu\text{s}$ 40 Rectangular Pulse	
$T_{stg}$ $T_j$	Storage and Junction Temperature Range	- 65 to + 150 - 65 to + 125	$^\circ\text{C}$ $^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering during 15s	260	$^\circ\text{C}$

#### THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction-leads	110	$^\circ\text{C/W}$

**ELECTRICAL CHARACTERISTICS**

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
I <sub>R</sub> *	T <sub>j</sub> = 25°C	V <sub>R</sub> = V <sub>RRM</sub>			0.5	mA
	T <sub>j</sub> = 100°C				10	
V <sub>F</sub> *	I <sub>F</sub> = 1A	T <sub>j</sub> = 25°C			0.7	V
	I <sub>F</sub> = 3A				1	

\* Pulse test: t<sub>p</sub> ≤ 300μs δ < 2%.

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	T <sub>j</sub> = 25°C	V <sub>R</sub> = 0		150		pF
	T <sub>j</sub> = 25°C	V <sub>R</sub> = 5V		40		

Forward current flow in a Schottky rectifier is due to majority carrier conduction. So reverse recovery is not affected by storage charge as in conventional PN junction diodes.

Nevertheless, when the device switches from forward biased condition to reverse blocking state, current is required to charge the depletion capacitance of the diode.

This current depends only of diode capacitance and external circuit impedance. Satisfactory circuit behaviour analysis may be performed assuming that Schottky rectifier consists of an ideal diode in parallel with a variable capacitance equal to the junction capacitance (see fig. 5 page 4/4).

Figure 1. Forward current versus forward voltage at low level (typical values).

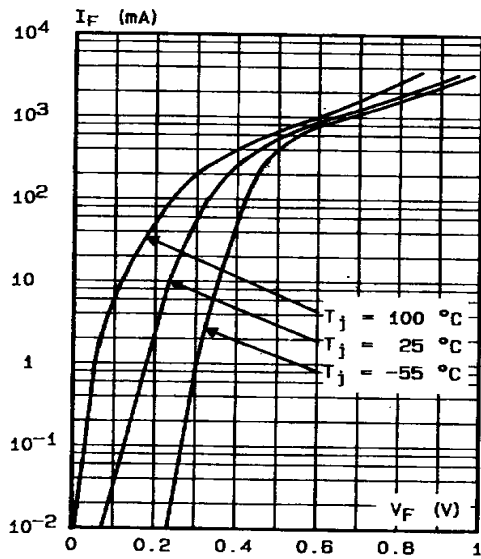


Figure 2. Forward current versus forward voltage at high level (typical values).

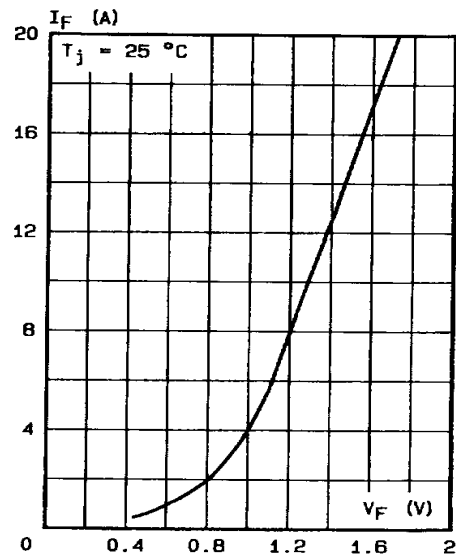


Figure 3. Reverse current versus junction temperature.

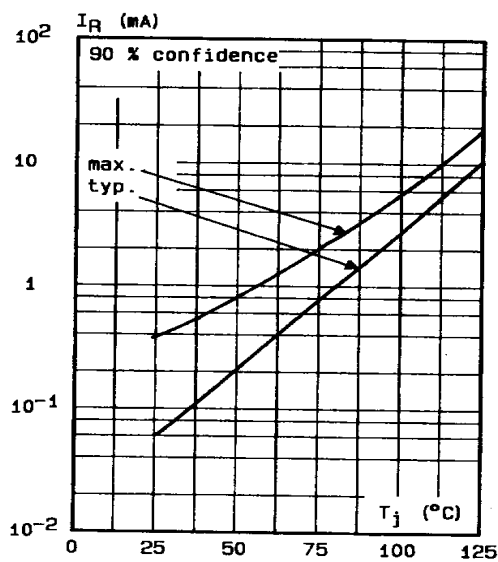


Figure 4. Reverse current versus  $V_{RRM}$  in per cent.

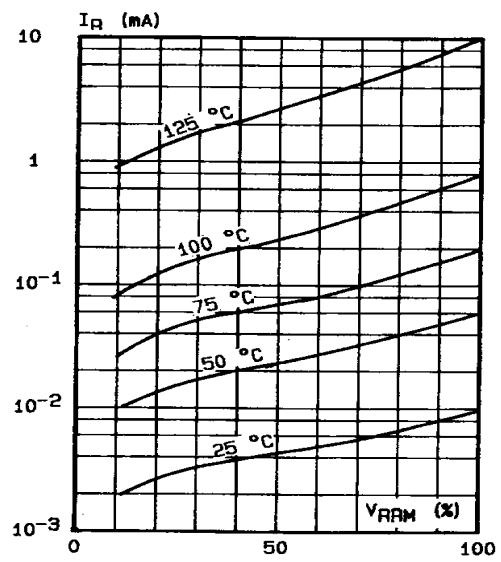


Figure 5. Capacitance C versus reverse applied voltage  $V_R$  (typical values)

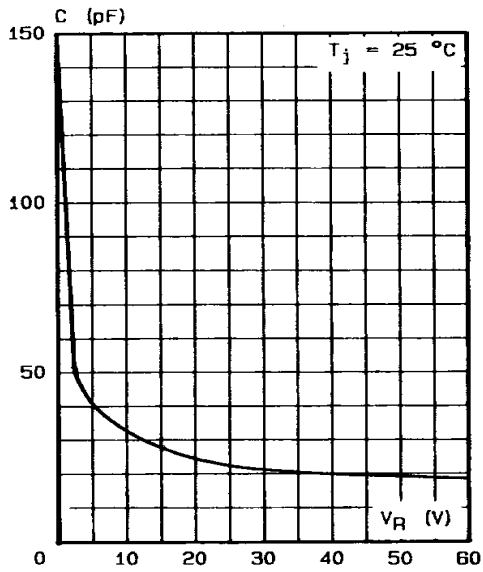


Figure 6. Surge non repetitive forward current for a rectangular pulse with  $t \leq 10$  ms.

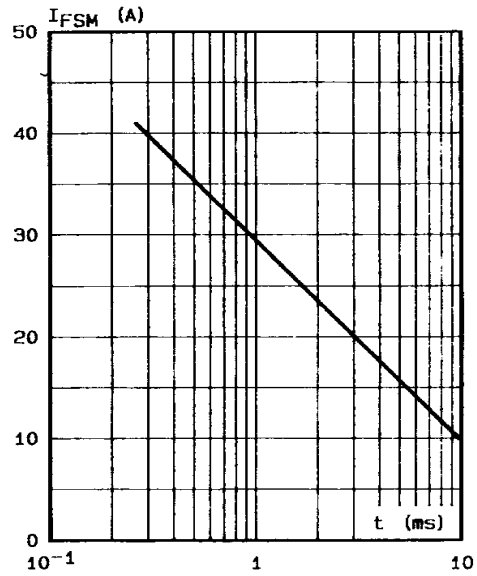
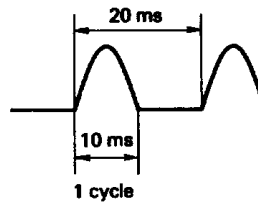
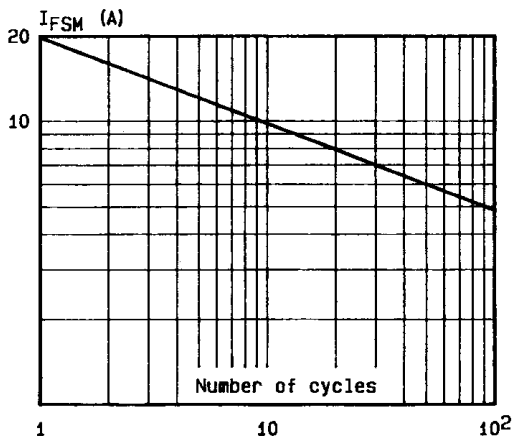
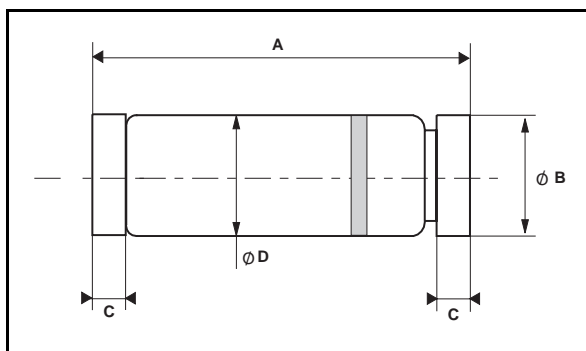


Figure 7. Surge non repetitive forward current versus number of cycles.



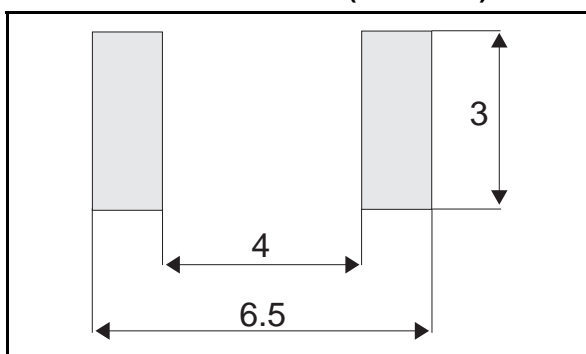
**PACKAGE MECHANICAL DATA**

MELF Glass



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.80		5.20	0.189		0.205
Ø B	2.50		2.65	0.098		0.104
C	0.45		0.60	0.018		0.024
Ø D		2.50			0.098	

**FOOT PRINT DIMENSIONS (Millimeter)**



Marking: ring at cathode end.  
Weight: 0.15g

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics  
© 1999 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES  
Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia  
Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - U.S.A.

<http://www.st.com>

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9